



40V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _C = +25°C
	11.5mΩ @ V _{GS} = 10V	30A
40V	17.8mΩ @ V _{GS} = 4.5V	24A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

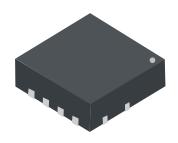
Features and Benefits

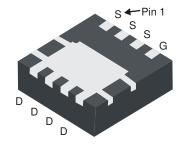
- 100% Unclamped Inductive Switching(UIS) Test in Production Ensures More Reliable And Robust End Application
- Low R_{DS(ON)} Ensures On State Losses Are Minimized
- Excellent Q_{gd x} R_{DS(ON)} Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

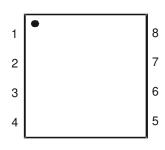
Mechanical Data

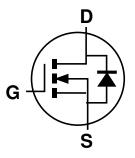
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)

PowerDI3333-8









Top View

Bottom View

Top View

Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT4011LFG-7	PowerDI3333-8	2,000/Tape & Reel
DMT4011LFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

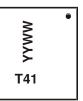
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site1:

PowerDI3333-8



T41 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 21 = 2021) WW = Week Code (01 to 53)

Site2:

X X X T41

T41 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 1 = 2021) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2015	 2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	5	 1	2	3	4	5	6	7	8	9	0

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Υ	Z



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage	V _{GSS}	+20 -16	V	
Continuous Drain Current (Note 5) VGS = 10V	ΙD	30 24	А	
Continuous Drain Current (Note 5) VGS = 10V	lο	10.8 8.6	Α	
Maximum Continuous Body Diode Forward Current (Note 5)		Is	2.1	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	65	Α	
Avalanche Current, L=0.3mH	I _{AS}	11.9	A	
Avalanche Energy, L=0.3mH		Eas	21.4	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	PD	2	W
Thermal Resistance, Junction to Ambient (Note 5)		RθJA	62	°C/W
Total Power Dissipation (Note 5)	Tc = +25°C	PD	15.6	W
Thermal Resistance, Junction to Case (Note 5)		Rejc	8	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (TA = +25°C, unless otherwise specified.)

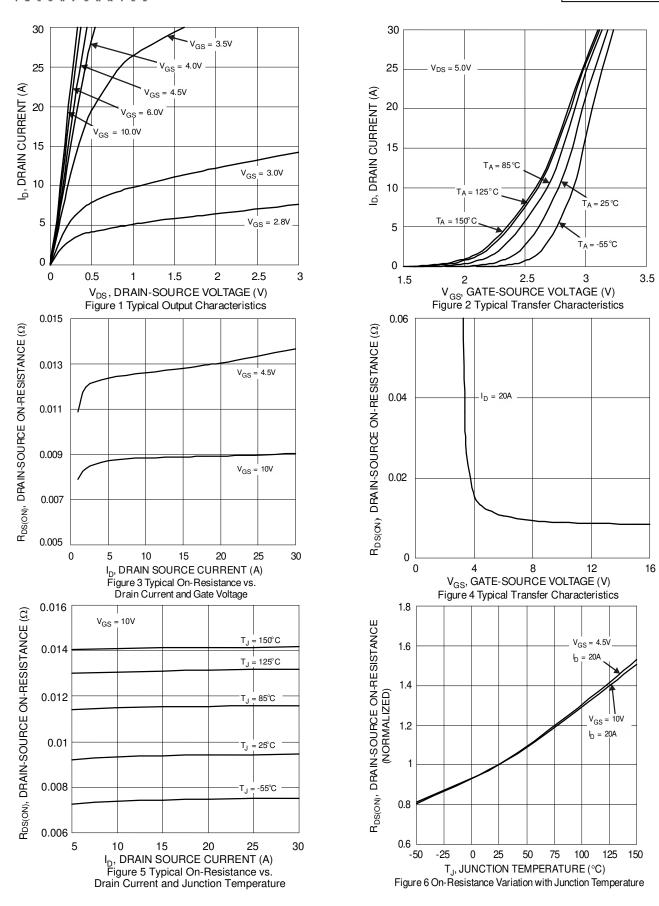
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	V _{DS} = 32V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	100 -100	nA	V _{GS} = +20V, V _{DS} = 0V V _{GS} = -16V, V _{DS} = 0V	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	0	_	9.2	11.5	m0	$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	RDS(ON)	_	13.4	17.8	mΩ	V _{GS} = 4.5V, I _D = 20A	
Diode Forward Voltage	VsD	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 7)						•	
Input Capacitance	Ciss	_	767	_		$V_{DS} = 20V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	_	238	_	рF		
Reverse Transfer Capacitance	Crss	_	30.6	_			
Gate Resistance	Rg	_	1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	7	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	15.1	_	0	V 00V I 00A	
Gate-Source Charge	Qgs	_	2.1	_	nC	$V_{DS} = 20V, I_{D} = 20A$	
Gate-Drain Charge	Q _{gd}	_	3.2	_			
Turn-On Delay Time	td(on)	_	3.5	_			
Turn-On Rise Time	tR		5.8			V _{DD} = 20V, V _{GS} = 10V,	
Turn-Off Delay Time			9.6		ns	$R_G = 1.6\Omega$, $I_D = 20A$	
Turn-Off Fall Time	tr		2				
Body Diode Reverse Recovery Time	t _{RR}		9.8		ns	1 45A -11/-14 400A/	
Body Diode Reverse Recovery Charge	Qrr	_	5.1	_	nC	I _F = 15A, di/dt = 400A/μs	

Notes: 5. $R_{0,JA}$ is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout. $R_{0,JC}$ is guaranteed by design while $R_{0,JA}$ is determined by the user's board design.

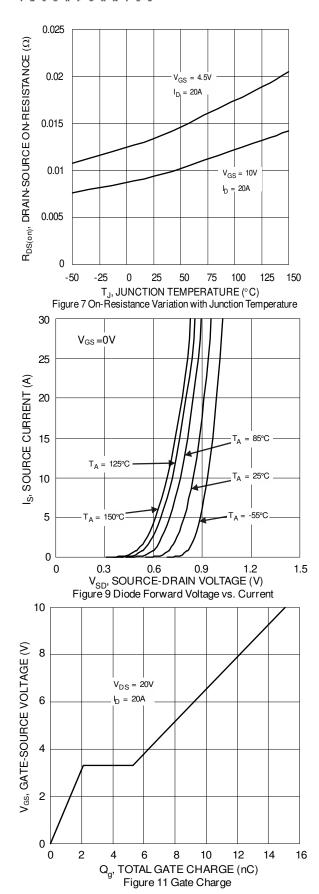
^{6.} Short duration pulse test used to minimize self-heating effect.

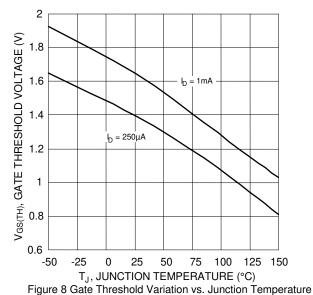
^{7.} Guaranteed by design. Not subject to product testing.

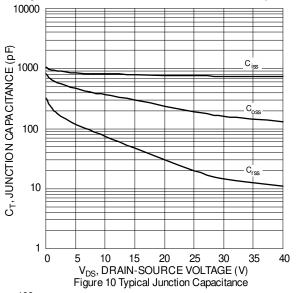


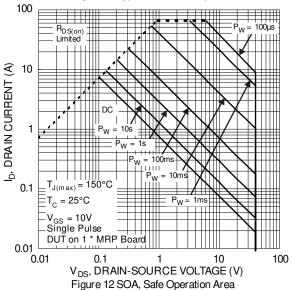




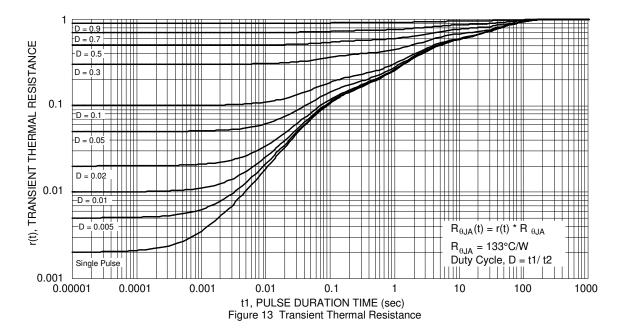










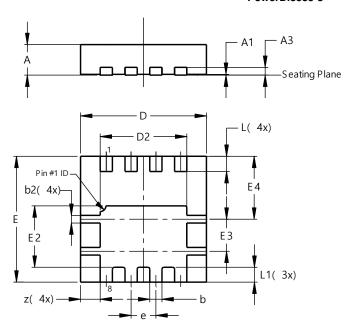




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

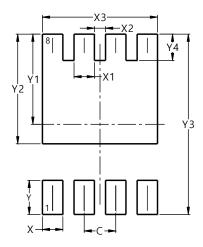


	PowerDI3333-8								
Dim	Min	Max	Тур						
Α	0.75	0.85	0.80						
A 1	0.00	0.05	0.02						
A 3	1	-	0.203						
b	0.27	0.37	0.32						
b2	0.15	0.25	0.20						
D	3.25	3.35	3.30						
D2	2.22	2.32	2.27						
Е	3.25	3.35	3.30						
E2	1.56	1.66	1.61						
E3	0.79	0.89	0.84						
E4	1.60	1.70	1.65						
е	-	_	0.65						
L	0.35	0.45	0.40						
L1	_	_	0.39						
Z	_	_	0.515						
All I	Dimens	sions ir	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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